1N5061 THRU 1N5062

SINTERED GLASS JUNCTION AVALANCHE RECTIFIER

VOLTAGE：600V to 800V **CURRENT: 2.0A**

GULF SEMI

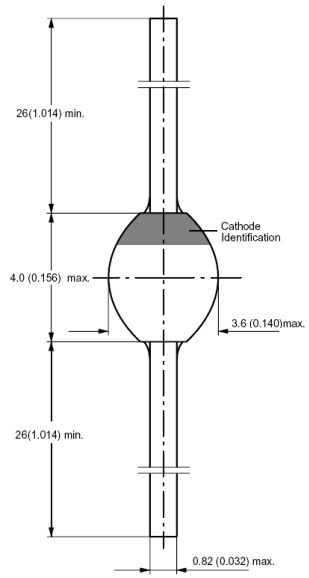
FEATURE

Glass passivated
High maximum operating temperature
Low leakage current
Excellent stability
Guaranteed avalanche energy absorption capability

MECHANICAL DATA

Case: SOD-57 sintered glass case
Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
Polarity: color band denotes cathode end
Mounting position: any

SOD-57



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	SYMBOL	1N5061	1N5062	units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	600	800	V
Maximum RMS Voltage	V_{RMS}	420	560	V
Maximum DC blocking Voltage	V_{DC}	600	800	V
Maximum Average Forward Rectified Current 3/8"lead length at Ttp =45°C	I_{FAV}	2.0		A
Peak Forward Surge Current at t=10ms half sinewave	I_{FSM}	50		A
Maximum Forward Voltage at rated Forward Current at 1.0A	V_F	1.0		V
Maximum DC Reverse Current Ta =25°C at rated DC blocking voltage Ta =165°C	I_R	1.0 150.0		μA
Typical Reverse Recovery Time (Note 1)	Trr	3000		nS
Diode capacitance at0V,1MHz	Cd	50		pF
Typical Thermal Resistance (Note 2)	$R_{th(ja)}$	100		K/W
Storage and Operating Junction Temperature	Tstg, Tj	-65 to +175		°C

Note:

1. Reverse Recovery Condition If =0.5A, Ir =1.0A, Irr =0.25A
2. Device mounted on epoxy-glass printed-circuit board, 1.5mm thick

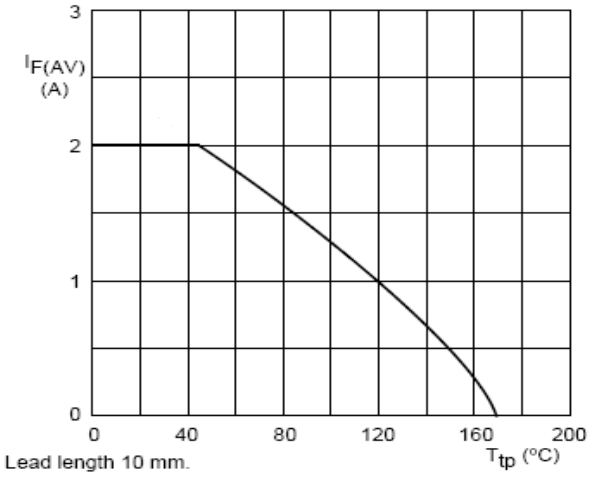


Fig.1 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

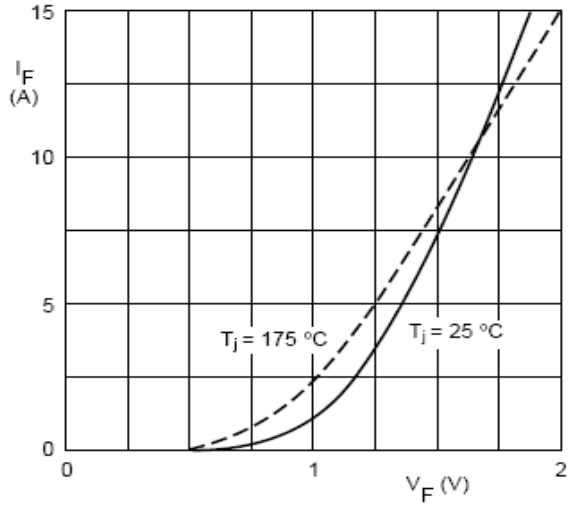


Fig.2 Forward current as a function of forward voltage; maximum values.

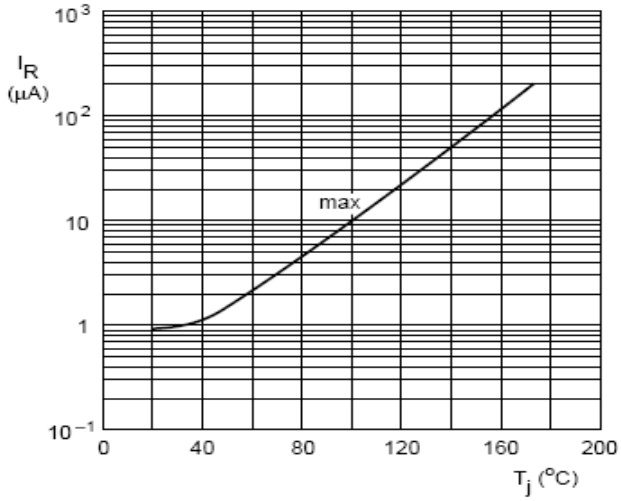


Fig.3 Reverse current as a function of junction temperature; maximum values.

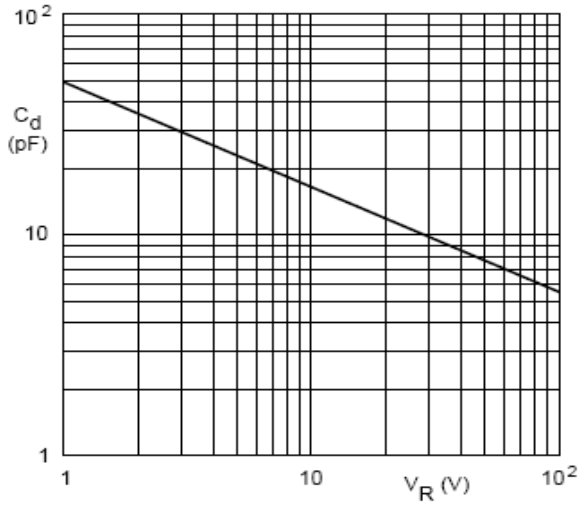


Fig.4 Diode capacitance as a function of reverse voltage; typical values.

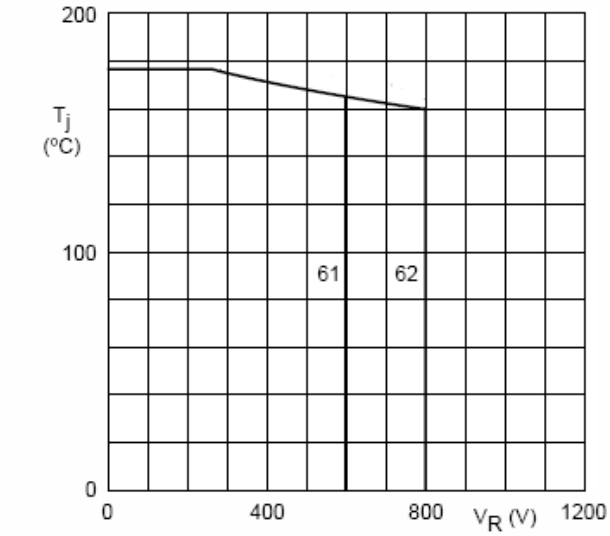


Fig.5 Maximum permissible junction temperature as a function of reverse voltage.